NTS260ESF, NRVTS260ESF

Very Low Forward Voltage Trench-based Schottky Rectifier

ON Semiconductor®

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TRENCH SCHOTTKY RECTIFIER
2.0 AMPERES
60 VOLTS

SOD−123FL
CASE 498

Features

- Fine Lithography Trench−based Schottky Technology for Very Low Forward Voltage and Low Leakage
- Fast Switching with Exceptional Temperature Stability
- Low Power Loss and Lower Operating Temperature
- Higher Efficiency for Achieving Regulatory Compliance
- Low Thermal Resistance
- High Surge Capability
- NRV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC−Q101 Qualified and PPAP Capable
- These Devices are Pb−Free, Halogen Free/BFR Free and are RoHS Compliant

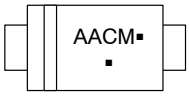
Mechanical Characteristics:

- Case: Molded Epoxy
- Epoxy Meets UL 94 V−0 @ 0.125 in
- Weight: 11.7 mg (Approximately)
- Lead and Mounting Surface Temperature for Soldering Purposes: 260°C Maximum for 10 Seconds
- MSL 1

Typical Applications

- Switching Power Supplies including Compact Adapters and Flat Panel Display
- High Frequency and DC−DC Converters
- Freewheeling and OR−ing diodes
- Reverse Battery Protection
- Instrumentation

MARKING DIAGRAM



AAC = Specific Device Code
M = Date Code
▪ = Pb−Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping†
NTS260ESFT3G	SOD−123FL (Pb−Free)	10,000/ Tape & Reel
NRVTS260ESFT3G	SOD−123FL (Pb−Free)	10,000/ Tape & Reel
NTS260ESFT1G	SOD−123FL (Pb−Free)	3,000/ Tape & Reel
NRVTS260ESFT1G	SOD−123FL (Pb−Free)	3,000/ Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	60	V
Average Rectified Forward Current (T_L = 128°C)	I_O	2.0	A
Peak Repetitive Forward Current (Square Wave, 20 kHz, T_L = 137°C)	I_{FRM}	4.0	A
Non−Repetitive Peak Surge Current (Surge Applied at Rated Load Conditions Halfwave, Single Phase, 60 Hz)	I_{FSM}	50	A
Storage and Operating Junction Temperature Range (Note 1)	T_{stg}, T_J	−65 to +175	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. The heat generated must be less than the thermal conductivity from Junction−to−Ambient: $dP_D/dT_J < 1/R_{\theta JA}$.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
Thermal Resistance, Junction−to−Lead (Note 2)	Ψ_{JCL}	24.4	°C/W
Thermal Resistance, Junction−to−Ambient (Note 2)	$R_{\theta JA}$	85	°C/W
Thermal Resistance, Junction−to−Ambient (Note 3)	$R_{\theta JA}$	330	°C/W

ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
Maximum Instantaneous Forward Voltage (Note 4) (I_F = 1.0 A, T_J = 25°C) (I_F = 2.0 A, T_J = 25°C) (I_F = 1.0 A, T_J = 125°C) (I_F = 2.0 A, T_J = 125°C)	V_F	 0.55 0.65 0.47 0.58	V
Maximum Instantaneous Reverse Current (Note 4) (Rated dc Voltage, T_J = 25°C) (Rated dc Voltage, T_J = 125°C)	I_R	 12 3	 μA mA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Mounted with 700 mm^2 copper pad size (Approximately 1 in^2) 1 oz FR4 Board.
3. Mounted with pad size approximately 20 mm^2 copper, 1 oz FR4 Board.
4. Pulse Test: Pulse Width ≤ 380 μs, Duty Cycle ≤ 2.0%.

TYPICAL CHARACTERISTICS

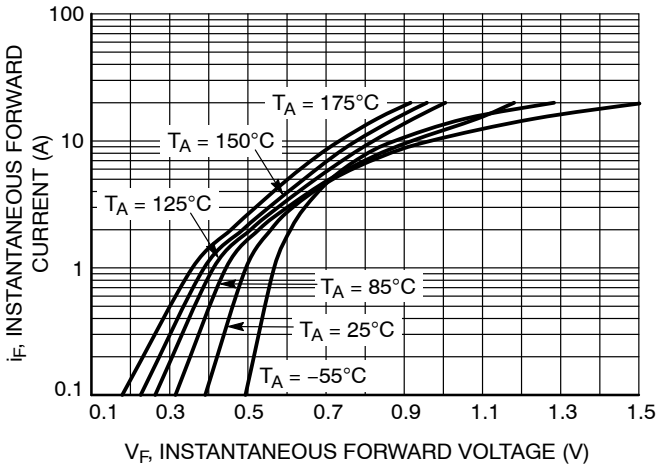


Figure 1. Typical Instantaneous Forward Characteristics

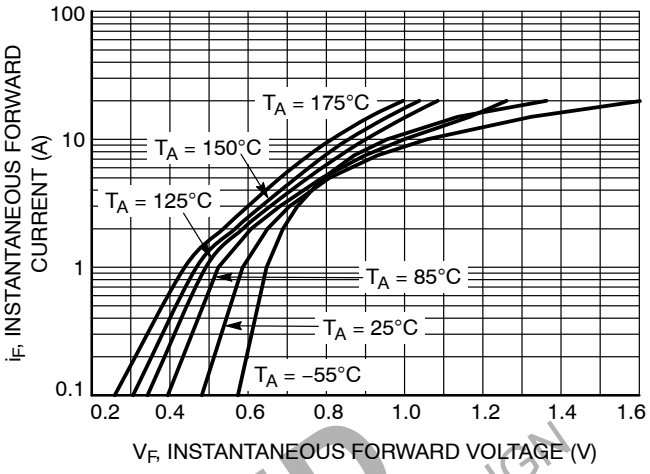


Figure 2. Maximum Instantaneous Forward Characteristics

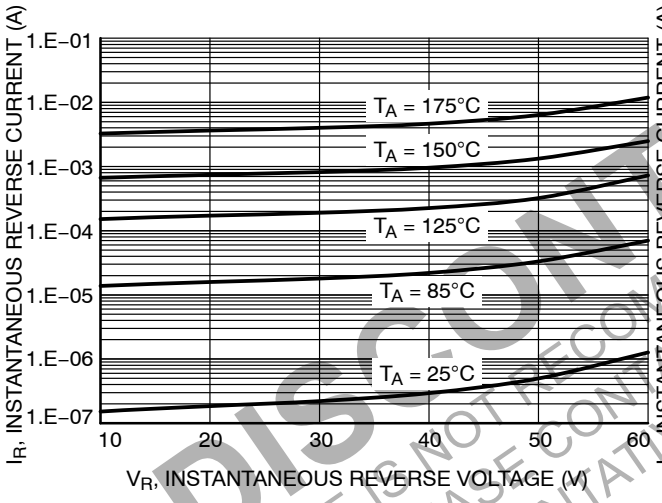


Figure 3. Typical Reverse Characteristics

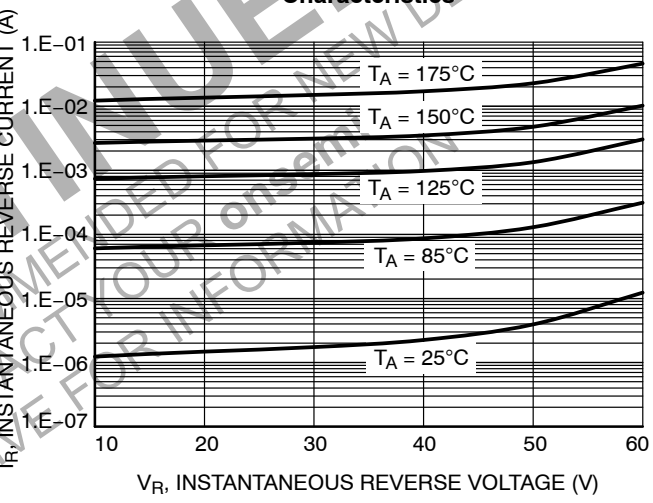


Figure 4. Maximum Reverse Characteristics

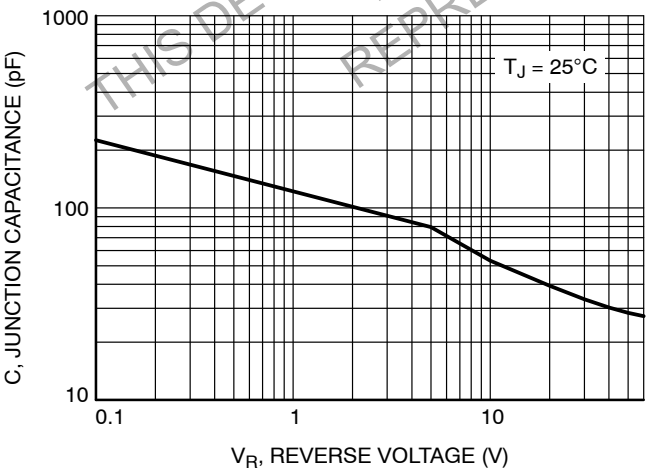


Figure 5. Typical Junction Capacitance

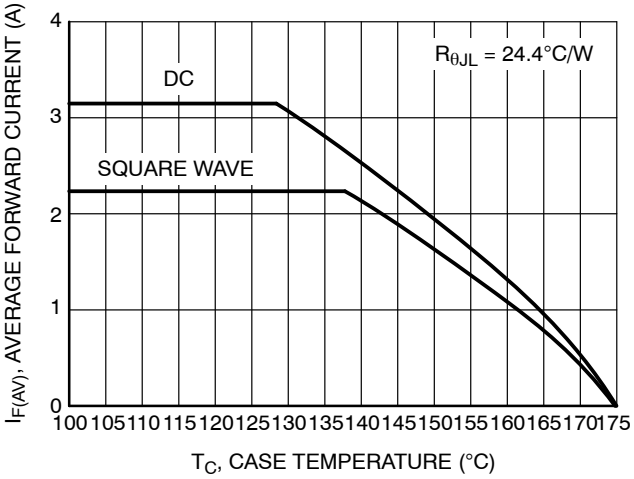
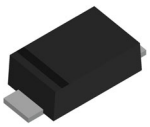
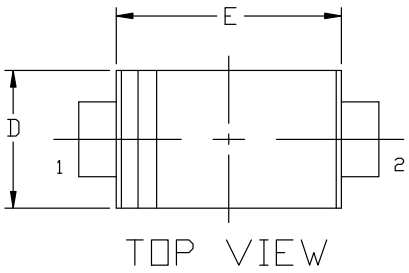


Figure 6. Current Derating

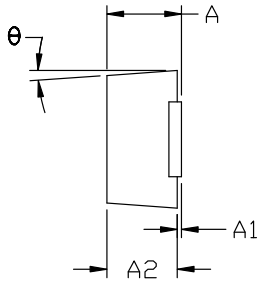


SOD−123−2 1.65x2.70x0.90
CASE 498
ISSUE E

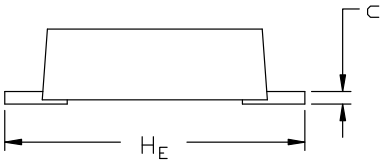
DATE 22 AUG 2023



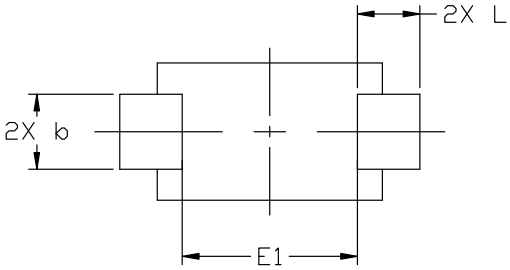
TOP VIEW



END VIEW



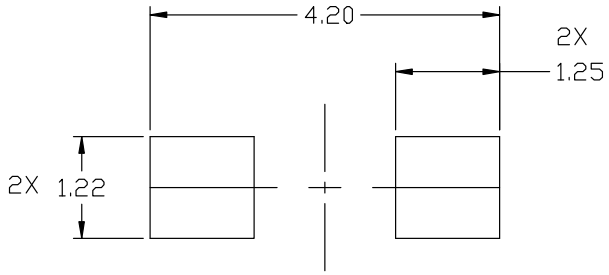
SIDE VIEW



BOTTOM VIEW

DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.90	0.95	0.98
A1	0.00	0.05	0.10
A2	0.85	0.90	0.95
b	0.70	0.90	1.10
c	0.10	0.15	0.20
D	1.50	1.65	1.80
E	2.50	2.70	2.90
E1	1.70	2.10	2.50
H_E	3.40	3.60	3.80
L	0.55	0.75	0.95
θ	0°	---	8°

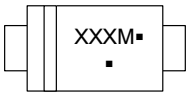
NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS
3. DIMENSIONS b AND L ARE TO BE MEASURED ON A FLAT SECTION OF THE LEAD BETWEEN 0.10 AND 0.25 FROM THE LEAD TIP.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH PROTRUSIONS, OR GATE BURRS.
5. FLAT LEAD.



RECOMMENDED
MOUNTING FOOTPRINT

* For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

GENERIC
MARKING DIAGRAM*



XXX = Specific Device Code
M = Date Code
▪ = Pb−Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “▪”, may or may not be present. Some products may not follow the Generic Marking.

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DESCRIPTION:	**SOD−123−2 1.65x2.70x0.90**		**PAGE 1 OF 1**

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